

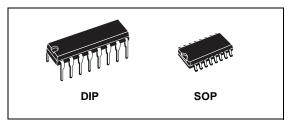
DIFFERENT 4-CHANNEL ANALOG MULTIPLEXER/DEMULTIPLEXER

- LOW "ON" RESISTANCE : 125Ω (Typ.) OVER 15V p.p SIGNAL-INPUT RANGE FOR V_{DD} - V_{EE} = 15V
- HIGH "OFF" RESISTANCE : CHANNEL LEAKAGE ± 100pA (Typ.) at V_{DD} - V_{EE} = 18V
- BINARY ADDRESS DECODING ON CHIP
- HIGH DEGREE OF LINEARITY : < 0.5% DISTORTION TYP. at $f_{IS} = 1$ KHz, $V_{IS} = 5$ V_{pp} , $V_{DD} - V_{SS} \ge 10$ V, RL = 10KΩ
- VERY LOW QUIESCENT POWER DISSIPATION UNDER ALL DIGITAL CONTROL INPUT AND SUPPLY CONDITIONS : 0.2 μW (Typ.) at V_{DD} - V_{SS} = V_{DD} - V_{EE} =10V
- MATCHED SWITCH CHARACTERISTICS : $R_{ON} = 5\Omega$ (Typ.) FOR V_{DD} - V_{EE} = 15V
- WIDE RANGE OF DIGITAL AND ANALOG SIGNAL LEVELS : DIGITAL 3 to 20, ANALOG TO 20V p.p.
- QUIESCENT CURRENT SPECIF. UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGSINPUT LEAKAGE CURRENT
- INPUT LEAKAGE CORRENT $I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C$ ■ 100% TESTED FOR QUIESCENT CURRENT
- 100% TESTED FOR QUIESCENT CURRENT MEETS ALL DECURRENTS OF JEDEC
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

The HCF4052B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor

PIN CONNECTION



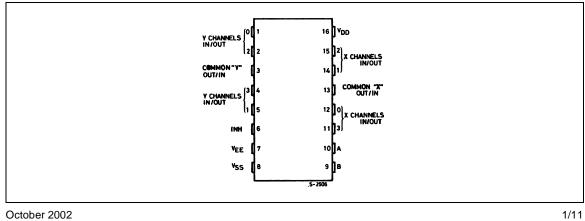
ORDER CODES

PACKAGE	TUBE	T & R
DIP	HCF4052BEY	
SOP	HCF4052BM1	HCF4052M013TR

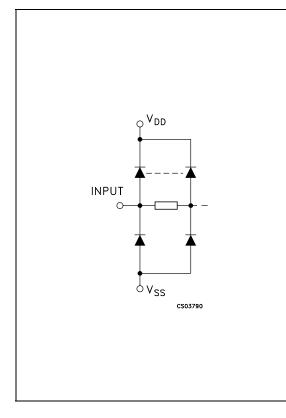
technology available in DIP and SOP packages.

The HCF4052B analog multiplexer/demultiplexer is a digitally controlled analog switch having low ON impedance and very low OFF leakage current. This multiplexer circuit dissipate extremely low quiescent power over the full V_{DD} - V_{SS} and V_{DD} - V_{EE} supply voltage range, independent of the logic state of the control signals.

When a logic "1" is present at the inhibit input terminal all channel are off. This device is a differential 4-channel multiplexer having two binary control inputs, A and B and an inhibit input. The two binary input signals selects 1 of 4 pairs of channels to be turned on and connect the analog inputs to the outputs.



INPUT EQUIVALENT CIRCUIT



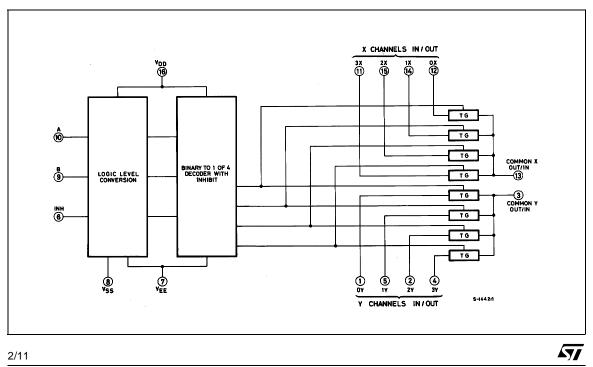
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
10, 9	A, B	Binary Control Inputs
6	INH	Inhibit Inputs
12, 14, 15, 11	0X to 3X CHANNEL IN/OUT	X channels Input/Output
1, 5, 2, 4	0Y to 3Y CHANNEL IN/OUT	Y channels Input/Output
3	COM Y OUT/ IN	Y Common Output/Input
13	COM X OUT/ IN	X Common Output/Input
7	V _{EE}	Supply Voltage
8	V _{SS}	Negative Supply Voltage
16	V _{DD}	Positive Supply Voltage

TRUTH TABLE

В	Α	
0	0	0x, 0y
0	1	1x, 1y
1	0	2x, 2y
1	1	3х, Зу
Х	Х	NONE
	B 0 1 1 X	B A 0 0 0 1 1 0 1 1 X X

X : Don't Care



FUNCTIONAL DIAGRAM

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	-0.5 to +22	V
VI	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
II.	DC Input Current	± 10	mA
PD	Power Dissipation per Package	500 (*)	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. All voltage values are referred to V_{SS} pin voltage. (*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	3 to 20	V
VI	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C



DC SPECIFICATIONS

		Test Condition				Value							
Symbol	Parameter	V _{IS}	V _{EE}	v _{ss}	V _{DD}	т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)	(V)	(V)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
١L	Quiescent Device				5		0.04	5		150		150	
	Current (all				10		0.04	10		300		300	μA
	switches ON or all switches OFF)				15		0.04	20		600		600	μА
					20		0.08	100		3000		3000	
SWITCH													
R _{ON}	Resistance	0 <u><</u> V∣ <u><</u>			5		470	1050		1200		1200	
		V_{DD}	0	0	10		180	400		520		520	Ω
		.00			15		125	280		360		360	
Δ_{ON}	Resistance Δ_{RON}	0 <u><</u> V _I ≤			5		10						
	(between any 2 of 4 switches)	V _{DD}	0	0	10		10						Ω
	,				15		5						
OFF*	Channel Leakage Current (All Channel OFF) (COMMON O/I)		0	0	18		±0.1	100		1000		1000	nA
OFF*	Channel Leakage Current (Any Channel OFF)		0	0	18		±0.1	100		1000		1000	nA
CI	Input Capacitance						5						
CO	Output Capacitance		-5	-5	5		18						pF
CIO	Feed through						0.2						
CONTRO	OL (Address or Inhi	bit)								•			
VIL	Input Low Voltage			= V _{SS}	5			1.5		1.5		1.5	
				1KΩ	10			3		3		3	V
		= VDD thru		V _{SS}	15			4		4		4	
V _{IH}	Input High Voltage	1KΩ	I _{IS} <	2μΑ	5	3.5			3.5		3.5		
				II OFF	10	7			7		7		V
			char	inels)	15	11			11		11		
I _{IH,} I _{IL}	Input Leakage Current	VI	= 0/18	V	18		±10 ⁻³	±0.1		±1		±1	μΑ
CI	Input Capacitance						5	7.5					pF

* Determined by minimum feasible leakage measurement for automating testing.

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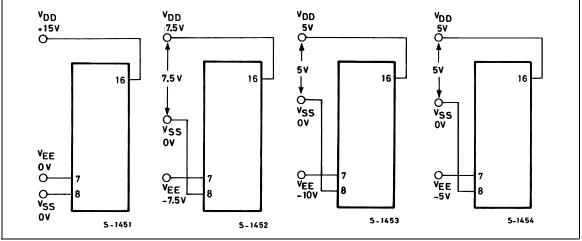
DYNAMIC ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$, $C_{L} = 50pF$, all input square wave rise and fall time = 20 ns)

	Test Condition								Value		
Parameter	V _{EE} (V)	R L (ΚΩ)	f _l (KHz)	V _I (V)	V _{SS} (V)	V _{DD} (V)		Min.	Тур.	Max.	
Propagation Delay				V		5			30	60	
Time (signal input to		200		V _{DD}		10			15	30	ns
output)						15			11	20	
Frequency Response Channel "ON" (sine	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		25		MHz
wave input) at 20 log V _O /V _I = - 3dB	- • 55	1		3()		10	V _O at any channel		60		101112
Feed through (all channels OFF) at	= V _{SS}	1		5(*)		10	V _O at Common OUT/IN		10		MHz
$20 \log V_{\rm O}/V_{\rm I} = -40 \rm dB$	- • 55	-		5()		10	V _O at any channel		8		1011 12
Frequency Signal Crosstalk at	= V _{SS}	1		5(*)		10	Between Sections (measured on common)		6		MHz
$20 \log V_O/V_I = -40 dB$	- • 55	I		5()		10	Between Sections (measured on any channel)		10		
Cine Mayo Distortion				2(*)		5			0.3		
Sine Wave Distortion $f_{IS} = 1 KHz$ Sine Wave	$= V_{SS}$	10	1	3(*)		10			0.2		%
				5(*)		15			0.12		
CONTROL (Address	or Inhibi	t)									
Propagation Delay:	0				0	5			360	720	
Address to Signal	0				0	10			160	320	ns
OUT (Channels ON or OFF)	0				0	15			120	240	115
	-5				0	5			225	450	
Propagation Delay:	0				0	5			360	720	
Inhibit to Signal OUT	0	1			0	10			160	320	ns
(Channel turning ON)	0	'			0	15			120	240	113
	-10				0	5			200	400	
Propagation Delay:	0					5			200	450	
Inhibit to Signal OUT	0	10				10			90	210	20
(Channel turning OFF)	0	10				15			70	160	ns
	-10					5			130	300]
Address or Inhibit to Signal Crosstalk	0	10 ⁽¹⁾			0	10	$V_{C} = V_{DD} - V_{SS}$ (square wave)		65		mV peak

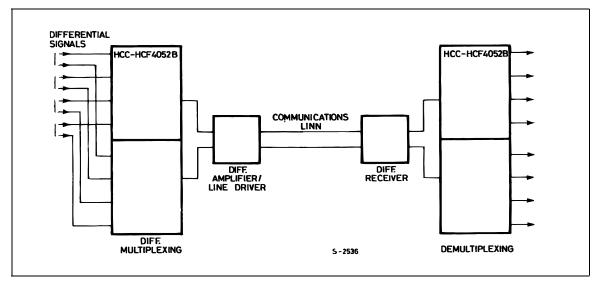
(1) Both ends of channel. * Peak to Peak voltage symmetrical about (V_{DD} - V_{EE}) /2



TYPICAL BIAS VOLTAGES



The ADDRESS (digtal-control inputs) and INHIBIT logic levels are : "0"=V_{SS} and "1"=V_{DD}. The analog signal (through the TG) may swing from V_{EE} to V_{DD}



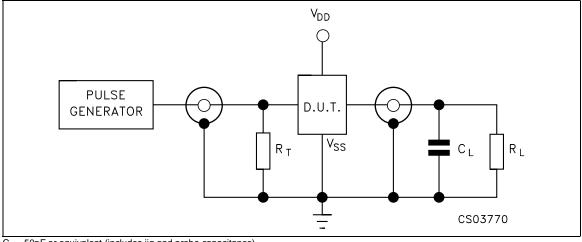
TYPICAL APPLICATIONS (TYPICAL TIME-DIVISION APPLICATION)

SPECIAL CONSIDERATIONS

Control of analog signals up to 20V peak to peak can be achieved by digital signal amplitudes of 4.5 to 20V (if $V_{DD} - V_{SS} = 3V$, a $V_{DD} - V_{EE}$ of up to 13V can be controlled; for $V_{DD} - V_{EE}$ level differences above 13V, a $V_{DD} - V_{SS}$ of at least 4.5V is required. For example, if $V_{DD} = +5$, $V_{SS} = 0$, and $V_{EE} = -13.5$, analog signals from -13.5V to 4.5V can be controlled by digital inputs of 0 to 4.5V. In certain applications, the external load resistor current may include both V_{DD} and signal-line components. To avoid drawing V_{DD} current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0,8V (calculated from R_{ON} values shown in DC SPECIFICATIONS). No V_{DD} current will flow through R_L if the switch current flows into leads 3 and 13.

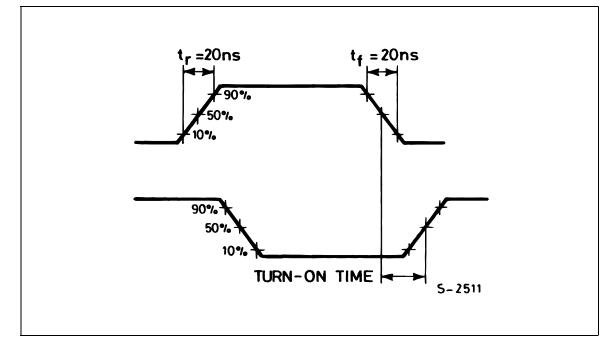
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TEST CIRCUIT

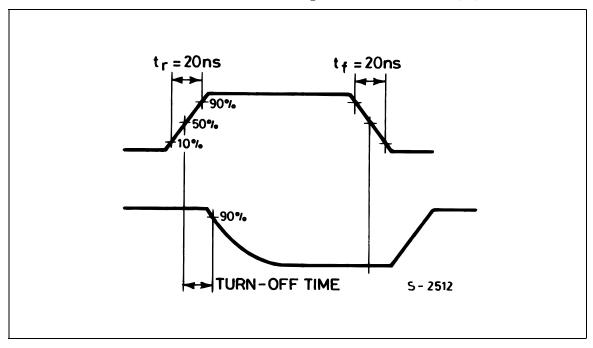


 $\begin{array}{l} C_L = 50 p F \mbox{ or equivalent (includes jig and probe capacitance)} \\ R_L = 200 K \Omega \\ R_T = Z_{OUT} \mbox{ of pulse generator (typically 50 \Omega)} \end{array}$

WAVEFORM 1 : CHANNEL BEING TURNED ON ($R_L = 1K\Omega$, f=1MHz; 50% duty cycle)



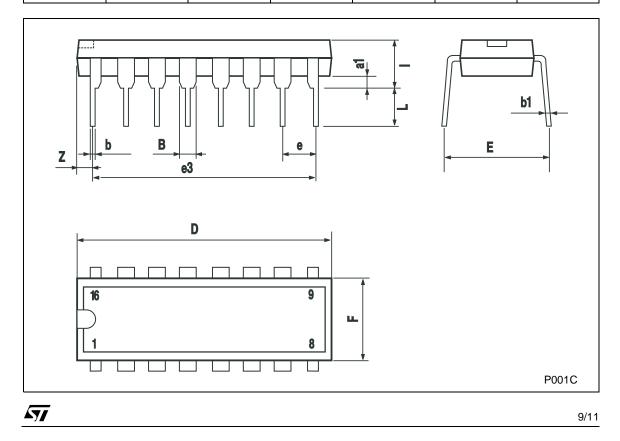
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WAVEFORM 2 : CHANNEL BEING TURNED OFF (R_L = 1K Ω , f=1MHz; 50% duty cycle)

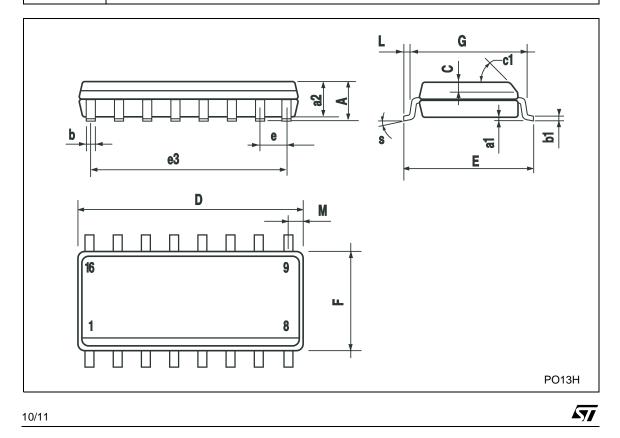
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	Plastic DIP-16 (0.25) MECHANICAL DATA										
DIM.		mm.			inch						
DIN.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.					
a1	0.51			0.020							
В	0.77		1.65	0.030		0.065					
b		0.5			0.020						
b1		0.25			0.010						
D			20			0.787					
E		8.5			0.335						
е		2.54			0.100						
e3		17.78			0.700						
F			7.1			0.280					
Ι			5.1			0.201					
L		3.3			0.130						
Z			1.27			0.050					



Γ

		SO-16 M	ECHANICA	L DATA			
DIM.		mm.		inch			
	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.	
А			1.75			0.068	
a1	0.1		0.2	0.003		0.007	
a2			1.65			0.064	
b	0.35		0.46	0.013		0.018	
b1	0.19		0.25	0.007		0.010	
С		0.5			0.019		
c1		•	45°	(typ.)	•		
D	9.8		10	0.385		0.393	
Е	5.8		6.2	0.228		0.244	
е		1.27			0.050		
e3		8.89			0.350		
F	3.8		4.0	0.149		0.157	
G	4.6		5.3	0.181		0.208	
L	0.5		1.27	0.019		0.050	
М			0.62			0.024	
S		•	8° (I	max.)	1	1	



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